

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
9 August 2001 (09.08.2001)

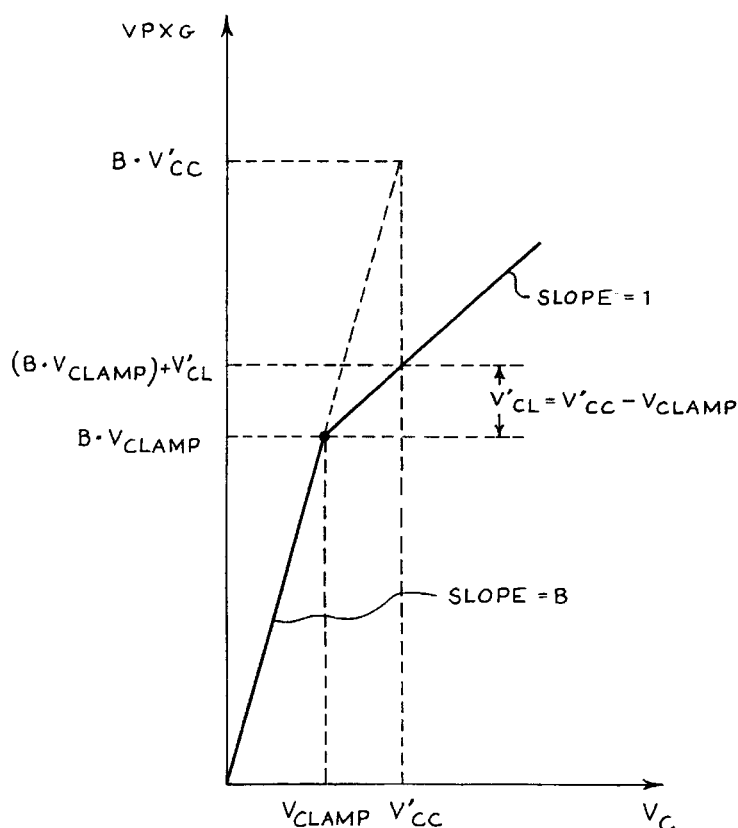
PCT

(10) International Publication Number
WO 01/57874 A3

- (51) International Patent Classification⁷: **G11C 5/14**, (72) Inventors: **AKAOGI, Takao**; 7911 October Way, Cupertino, CA 95014 (US). **AL-SHAMMA, Ali, K.**; 2966 Moorpark #10, San Jose, CA 95128 (US). **CLEVELAND, Lee, Edward**; 3428 St. Mary's Place, Santa Clara, CA 95051 (US). **KIM, Yong**; 3450 Warburton Avenue #10, Santa Clara, CA 95051 (US). **LIN, Jin-Lien**; 20800 Homestead Road #32C, Cupertino, CA 95014 (US). **TEH, Boon, Tang**; 570 Mill Creek Lane #203, Santa Clara, CA 95054 (US). **NGUYEN, Kendra**; 4942 Zeppelin Court, San Jose, CA 95111 (US).
- (21) International Application Number: PCT/US01/40031
- (22) International Filing Date: 5 February 2001 (05.02.2001)
- (25) Filing Language: English
- (26) Publication Language: English
- (30) Priority Data:
60/180,638 7 February 2000 (07.02.2000) US
09/595,519 16 June 2000 (16.06.2000) US
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- (81) Designated States (*national*): CN, JP, KR, SG.
- (84) Designated States (*regional*): European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR).

[Continued on next page]

(54) Title: VOLTAGE BOOST LEVEL CLAMPING CIRCUIT FOR A FLASH MEMORY



(57) Abstract: A voltage boost circuit (111) for a flash memory (100) includes a boosting circuit (110), which is capable of boosting a portion of a power supply voltage (V_{CC}) of the flash memory to a word line voltage level adequate for accessing a core cell in a core cell array (102) of the memory. The voltage boost circuit further includes a balancing or clamping circuit (112) for providing a nonzero adjustment voltage (V_{CL}) to the boosting circuit to reduce the portion of the supply voltage that is available for boosting by the boosting circuit when the power supply voltage exceeds a certain value.



Published:

— with international search report

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(88) Date of publication of the international search report:

18 April 2002